

REMARKS

Claims 1, 2 and 4-22 are pending in this application. Claims 1, 7, 10, 21 and 22 are independent claims. By this secondary supplemental amendment: claims 7-9 and 22 are amended for clarity and to address typographical and grammatical errors made therein. Reconsideration in view of the above secondary supplemental amendments is respectfully solicited.

In view of the foregoing, Applicants respectfully submit that the application is in condition for allowance. Favorable reconsideration and prompt allowance are earnestly solicited.

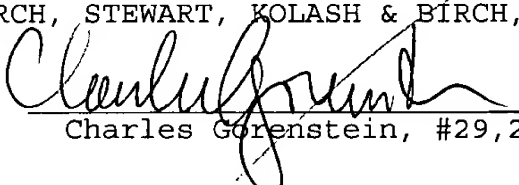
Should the Examiner believe that anything further would be desirable to place this application in better condition for allowance, the Examiner is invited to contact Carolyn T. Baumgardner (Reg. No. 41,345) at (703) 205-8000 to schedule a Personal Interview.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment from or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. §1.16 or under 37 C.F.R. §1.17; particularly, the extension of time fees.

Respectfully submitted,

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By


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CG/CTB/mpe
1248-0538P

Attachment: Version with Markings to Show Changes Made

VERSION WITH MARKINGS SHOWING CHANGES MADE

IN THE CLAIMS:

The claims are amended as follows:

7. (Three Times Amended) A method of manufacturing a semiconductor device, comprising the steps of:[,]

(i) securing a semiconductor element having an integrated circuit to a board so that the semiconductor element is maintained in a level position;[,]

(ii) subjecting at least a part of a back of the semiconductor element to processing, wherein the processing applies a stress to the semiconductor element, causing at least a part of the semiconductor element to deform when removed from the board,

wherein the semiconductor element operates normally only when the semiconductor device is maintained in a level position.

8. (Three Times Amended) The method of manufacturing a semiconductor device as defined in claim 7,

wherein the [processing] step (ii) is specified to be carried out by at least one technique selected from a group consisting of scraping by means of dicing, sand blast, and sandpaper and treatment by means of laser beam projection.

9. (Three Times Amended) The method of manufacturing a semiconductor device as defined in claim 7, wherein the [processing] step (ii) results in the semiconductor element having a thickness of 50 μm or less where the semiconductor element is processed.

22. (Twice Amended) A method of manufacturing a semiconductor device, comprising the steps of:

(a) securing a semiconductor element having an integrated circuit to a board so [as to be level with the board] that the semiconductor element is maintained in a level position; [,]

(b) subjecting at least a part of a back of the semiconductor element to processing, wherein the processing applies a stress to the semiconductor element, causing at least a part of the semiconductor element to deform when removed from the board,

wherein the [subjecting at least a part of a back to processing] step (b) is specified to be carried out by at least one technique selected from a group consisting of scraping by means of dicing, sand blast, and sandpaper and treatment by means of laser beam projection.